

ABSTRACT OF THE DISCLOSURE

To form a polycrystalline silicon film having a grain size of 1 μm or greater by means of laser annealing. A beam emitted from a laser apparatus (101) is split in two by a half mirror. The split beams are processed into linear shapes by cylindrical lenses (102) to (105), and (207), then simultaneously irradiate an irradiation surface (209). If an amorphous silicon film formed on a glass substrate is disposed on the irradiation surface (209), an area will be irradiated by both a linear shape beam entering from a front surface and a linear shape beam that has transmitted through the glass surface. Both linear shape beams irradiate the same area to thereby crystallize the amorphous silicon film.